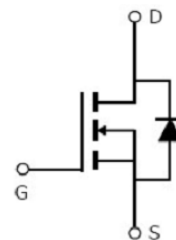


Main Product Characteristics:

V_{DSS}	40V
$R_{DS(on)}$	3.2mohm(typ.)
I_D	145A


TO-252

Marking and pin Assignment

Schematic diagram
Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 175°C operating temperature


Description:

It utilizes the latest trench processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications

Absolute max Rating:

Symbol	Parameter	Max.	Units
$I_D @ TC = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	145①	A
$I_D @ TC = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	100①	
I_{DM}	Pulsed Drain Current ②	580	
$P_D @ TC = 25^\circ C$	Power Dissipation ③	153	W
	Linear Derating Factor	1.02	W/°C
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy @ $L=0.1mH$	281.3	mJ
I_{AS}	Avalanche Current @ $L=0.1mH$	75	A
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 175	°C

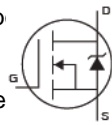
Thermal Resistance

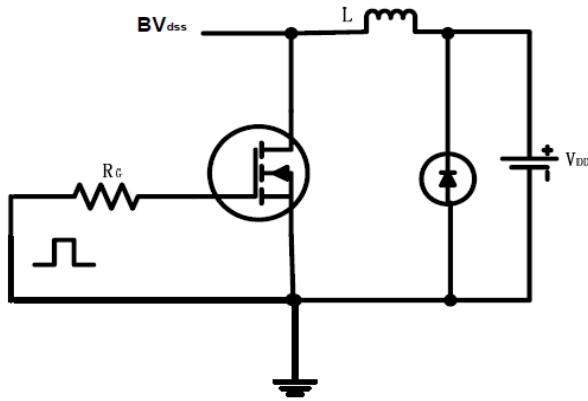
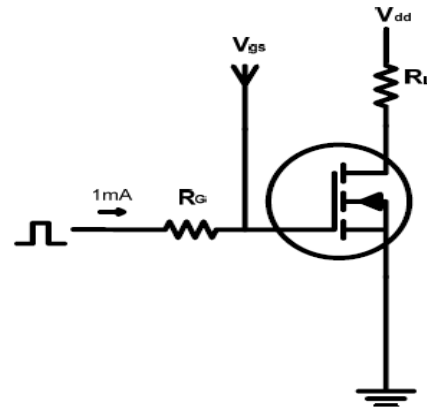
Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ③	—	0.98	$^{\circ}C/W$
$R_{\theta JA}$	Junction-to-ambient ($t \leq 10s$) ④	—	62	$^{\circ}C/W$
	Junction-to-Ambient (PCB mounted, steady-state) ④	—	40	$^{\circ}C/W$

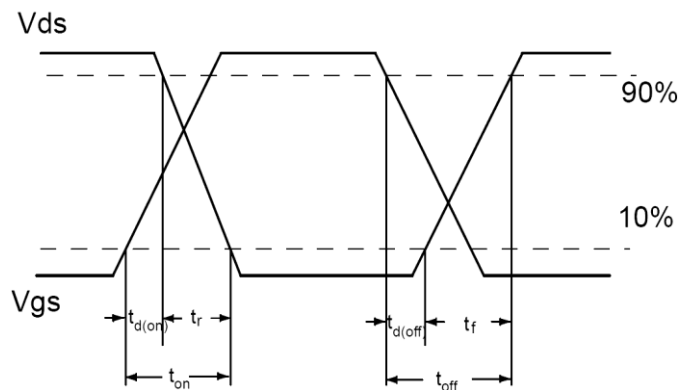
Electrical Characterizes @ $T_A=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	3.2	4	m Ω	$V_{GS}=10V, I_D = 30A$
		—	6.17	—		$T_J = 125^{\circ}C$
$V_{GS(th)}$	Gate threshold voltage	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
		—	1.11	—		$T_J = 125^{\circ}C$
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	50		$T_J = 125^{\circ}C$
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 20V$
		—	—	-100		$V_{GS} = -20V$
Q_g	Total gate charge	—	52.3	—	nC	$I_D = 20A,$ $V_{DS}=15V,$ $V_{GS} = 4.5V$
Q_{gs}	Gate-to-Source charge	—	20.3	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	23.1	—		
$t_{d(on)}$	Turn-on delay time	—	15.9	—	nS	$V_{GS}=10V, V_{DS}=15V,$ $R_L=0.75\Omega,$ $R_{GEN}=3\Omega$ $I_D=20A$
t_r	Rise time	—	49.0	—		
$t_{d(off)}$	Turn-Off delay time	—	61.6	—		
t_f	Fall time	—	25.6	—		
C_{iss}	Input capacitance	—	6653	—	pF	$V_{GS} = 0V$ $V_{DS} = 15V$ $f = 1MHz$
C_{oss}	Output capacitance	—	632	—		
C_{riss}	Reverse transfer capacitance	—	603	—		

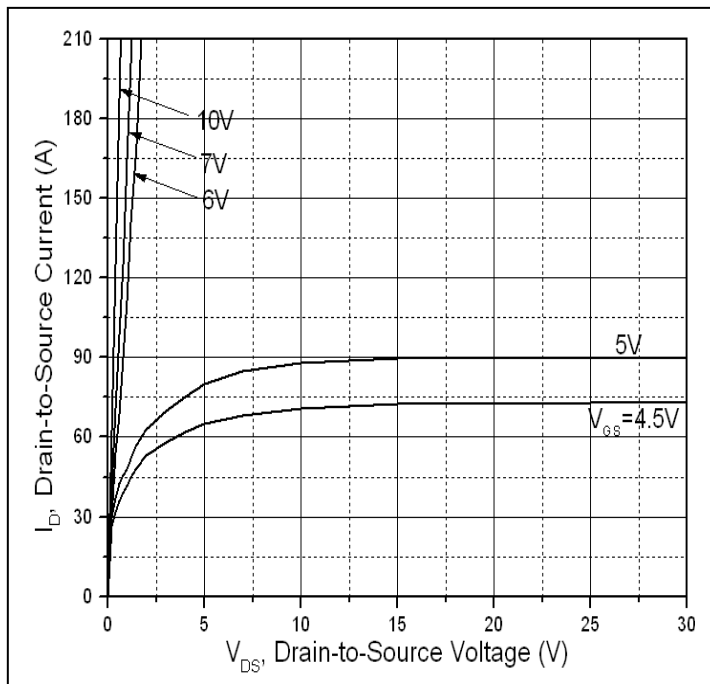
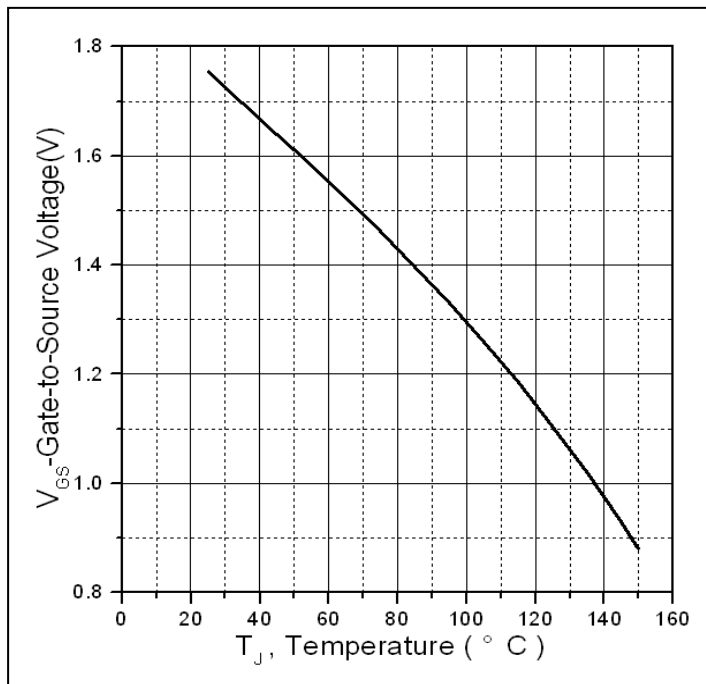
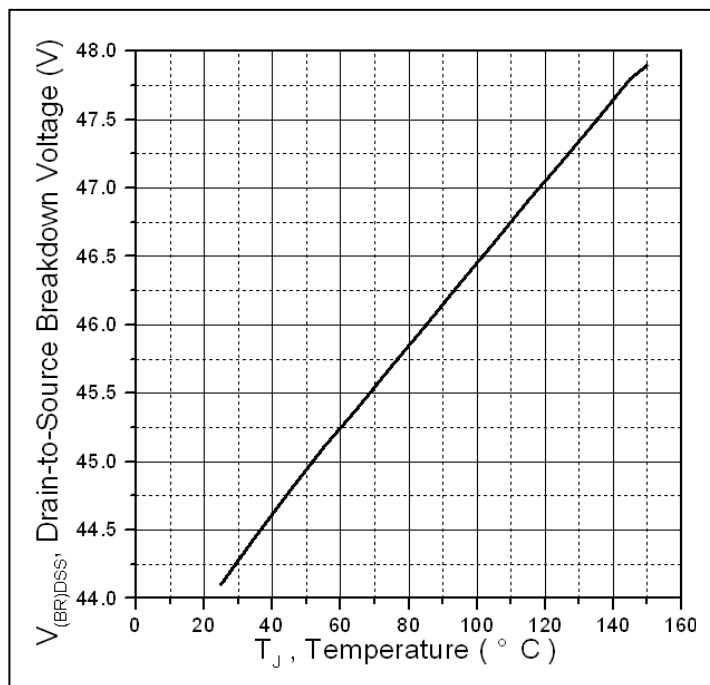
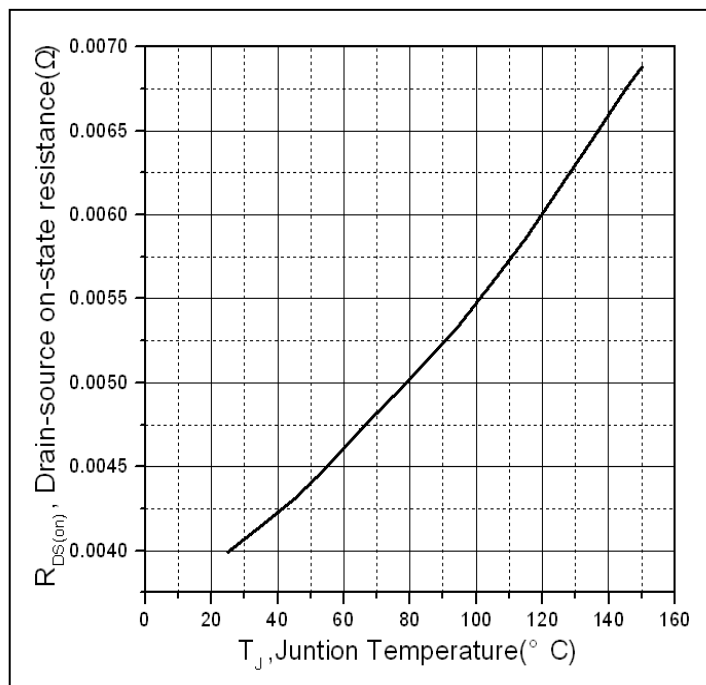
Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	145①	A	MOSFET symb showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	580	A	
V_{SD}	Diode Forward Voltage	—	0.72	1.2	V	$I_S=2.1A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	—	30.8	—	nS	$T_J = 25^{\circ}C, I_F = 20A, di/dt =$ $100A/\mu s$
Q_{rr}	Reverse Recovery Charge	—	31.1	—	nC	

Test circuits and Waveforms
EAS test circuits:

Gate charge test circuit:

Switch Time Test Circuit:

Switch Waveforms:

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.
- ⑤ These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)} = 175^\circ\text{C}$.

Typical electrical and thermal characteristics

Figure 1: Typical Output Characteristics

Figure 2. Gate to source cut-off voltage

Figure 3. Drain-to-Source Breakdown Voltage vs. Temperature

Figure 4: Normalized On-Resistance Vs. Case Temperature

Typical electrical and thermal characteristics

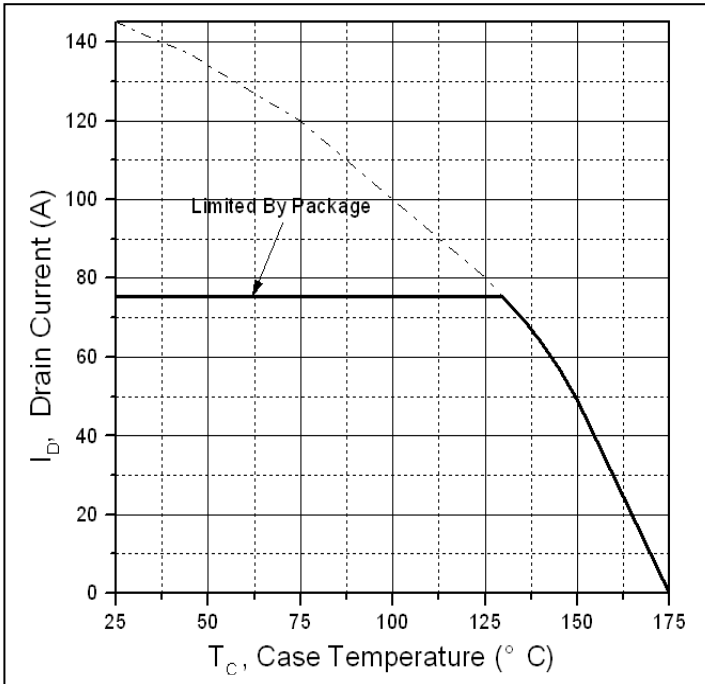


Figure 5. Maximum Drain Current Vs. Case Temperature

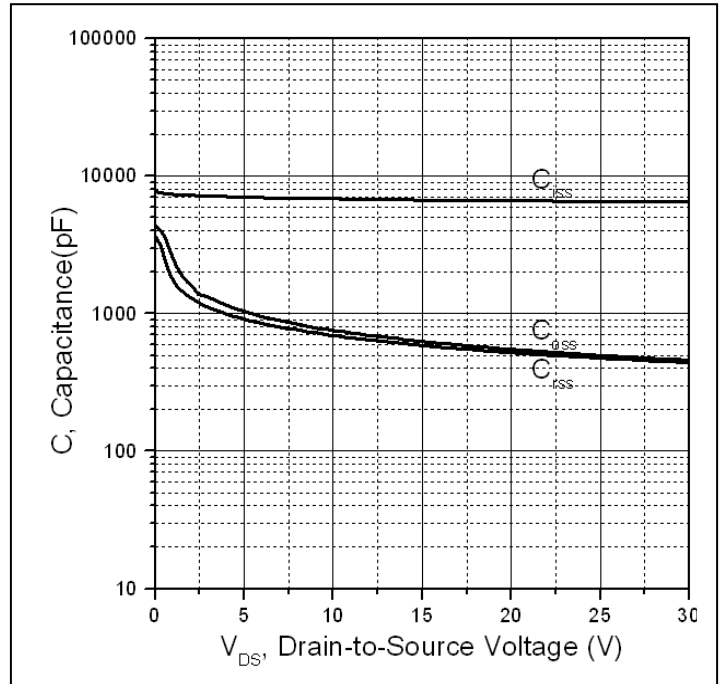


Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

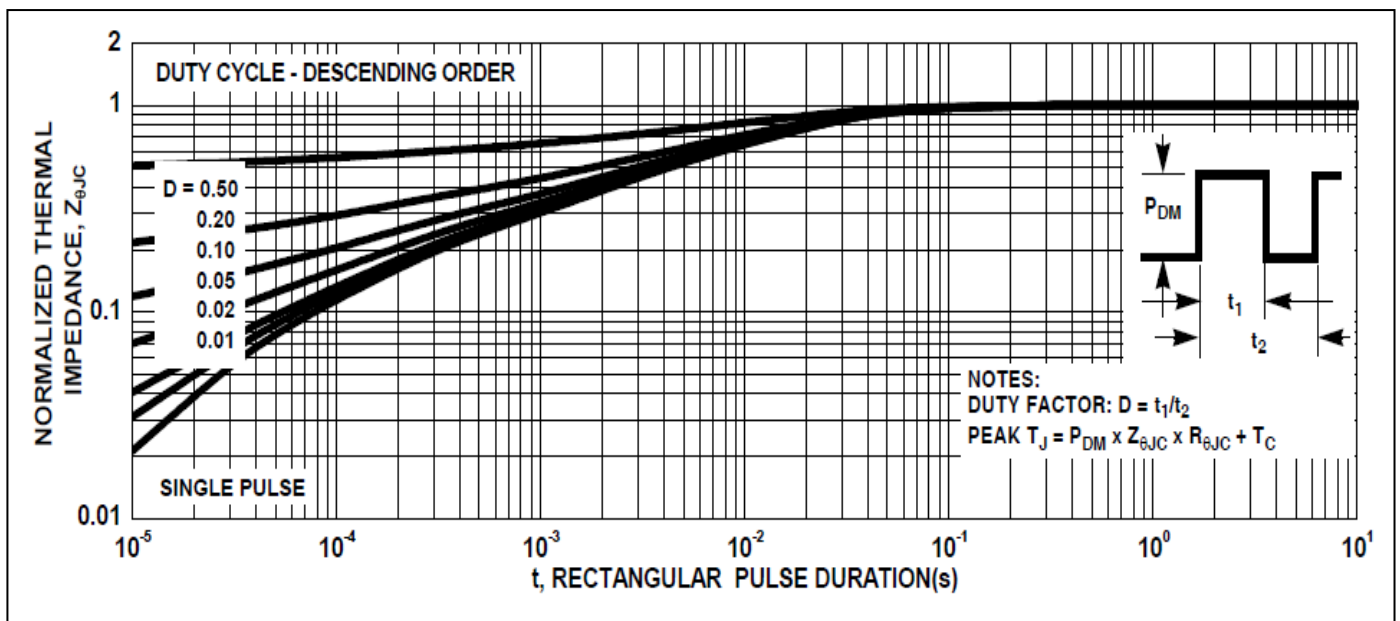
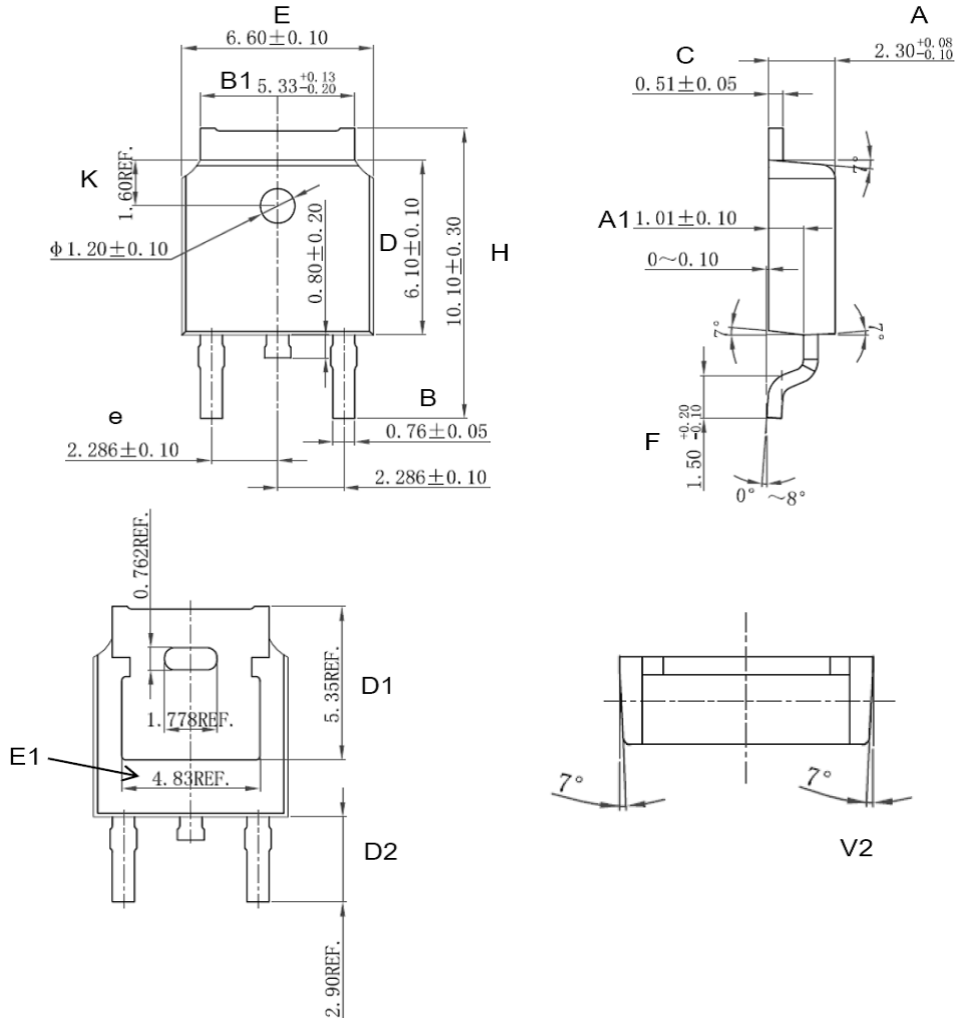


Figure 7. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Mechanical Data:
DPAK PACKAGE OUTLINE DIMENSION


Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	2.200	2.300	2.380	0.087	0.091	0.094
A1	0.910	1.010	1.110	0.036	0.040	0.044
B	0.710	0.760	0.810	0.028	0.030	0.032
B1	5.130	5.330	5.460	0.202	0.210	0.215
C	0.460	0.510	0.560	0.018	0.020	0.022
D	6.000	6.100	6.200	0.236	0.240	0.244
D1	5.350 (REF)			0.211 (REF)		
D2	2.900 (REF)			0.114 (REF)		
E	6.500	6.600	6.700	0.256	0.260	0.264
E1	4.83 (REF)			0.190 (REF)		
e	2.186	2.286	2.386	0.086	0.090	0.094
H	9.800	10.100	10.400	0.386	0.398	0.409
F	1.400	1.500	1.700	0.055	0.059	0.067
K	1.600 (REF)			0.063 (REF)		
V2	8° (REF)			8° (REF)		

Ordering and Marking Information
Device Marking: SSFD4004

Package (Available)
DPAK (TO-252)
Operating Temperature Range
C : -55 to 175 °C

Devices per Unit
Option1:

Package Type	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO-252	2500	2	5000	7	35000

Option2:

Package Type	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO-252	2500	1	2500	10	25000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	$T_j=125^{\circ}\text{C}$ to 175°C @ 80% of Max $V_{DSS}/V_{CES}/V_R$	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	$T_j=150^{\circ}\text{C}$ or 175°C @ 100% of Max V_{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices

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